PROCESS CP593

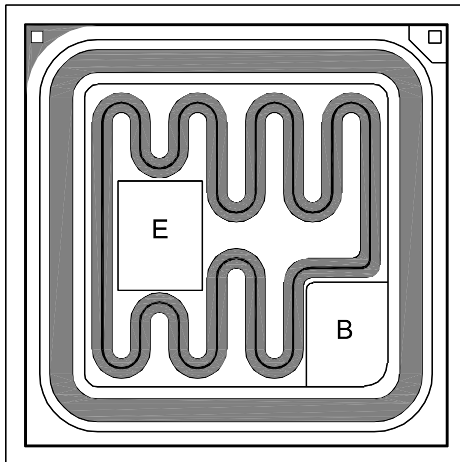
Small Signal Transistor

PNP - Amp/Switch Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	19 x 19 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	3.5 x 4.3 MILS
Emitter Bonding Pad Area	3.5 x 4.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



R1

BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

30,475

PRINCIPAL DEVICE TYPES

2N4403
2N5366

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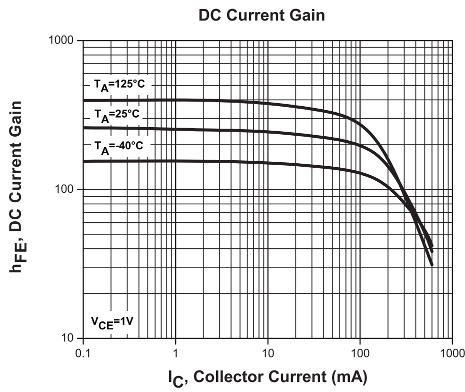
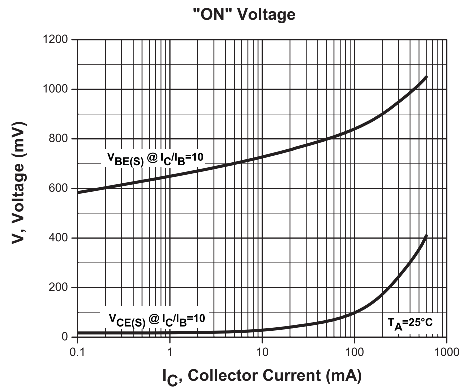
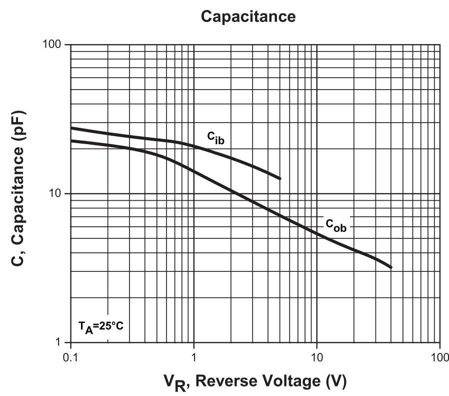
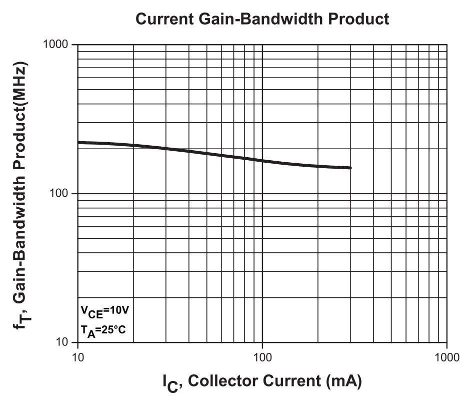
PROCESS CP593

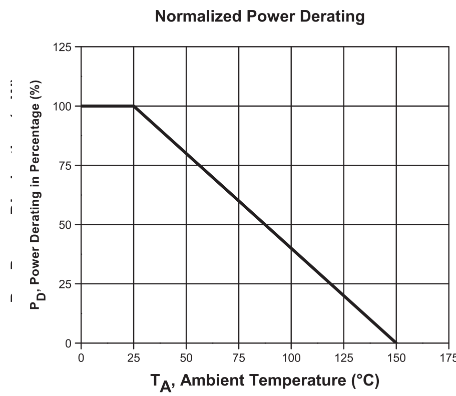
Typical Electrical Characteristics











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